

## **isc** Silicon NPN Power Transistor

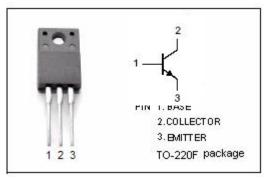
# INCHANGE SEMICONDUCTOR 2SD2374

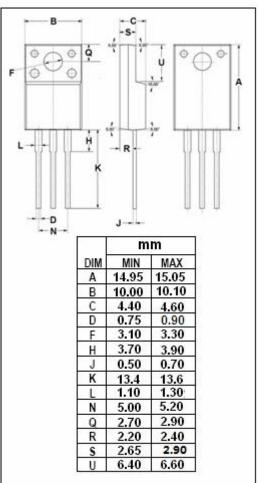
### DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= 60V(Min)
- Collector Power Dissipation-:  $P_C$ = 25 W@  $T_C$ = 25 °C
- Low Collector Saturation Voltage-
- :  $V_{CE(sat)^{=}}$  1.2V(Max)@ (I<sub>C</sub>= 3A, I<sub>B</sub>= 0.375A)
- Complement to Type 2SB1548
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

## APPLICATIONS

• Designed for power amplifications.





### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

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SYMBOL	PARAMETER	VALUE	UNIT			
V <sub>сво</sub>	Collector-Base Voltage	60	V			
V <sub>CEO</sub>	Collector-Emitter Voltage	60	V			
V <sub>EBO</sub>	Emitter-Base Voltage	6	V			
Ι <sub>C</sub>	Collector Current-Continuous	3	А			
I <sub>CM</sub>	Collector Current-Peak	5	А			
Pc	Collector Power Dissipation @Ta=25°C	2	W			
	Collector Power Dissipation @T <sub>c</sub> =25°C	25				
TJ	Junction Temperature	150	Ĉ			
T <sub>stg</sub>	Storage Temperature	-55~150	°C			



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### **ELECTRICAL CHARACTERISTICS**

#### Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 30mA; I <sub>B</sub> = 0	60			V
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 0.375A			1.2	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 3A; V <sub>CE</sub> = 4V			1.8	V
I <sub>CES</sub>	Collector Cutoff Current	V <sub>CE</sub> = 60V; V <sub>BE</sub> = 0			200	μ Α
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = 30V; I <sub>B</sub> = 0			300	μA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 6V; I <sub>C</sub> = 0			1	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 4V	70		250	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 3A; V <sub>CE</sub> = 4V	10			
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.5A;V <sub>CE</sub> = 10V; f <sub>test</sub> = 10MHz		30		MHz

#### h<sub>FE-1</sub> Classifications

Q	Р	
70-150	120-250	

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